

L Number	Hits	Search Text	DB	Time stamp
1	155	((ldd or (lightly near2 dop\$3)) same (source and drain)) near10 simultan\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 14:27
2	65	((ldd or (lightly near2 dop\$3)) same (source and drain)) near5 simultan\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 14:32
3	91	((ldd or (lightly near2 dop\$3)) same (source and drain)) near5 (simultan\$6 or "same" adj time)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 14:33
4	26	((((ldd or (lightly near2 dop\$3)) same (source and drain)) near5 (simultan\$6 or "same" adj time)) not (((ldd or (lightly near2 dop\$3)) same (source and drain)) near5 simultan\$6))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 14:33
7	2	6452241.URPN.	USPAT	2004/08/11 14:35
8	2	("5914498"   "6259120").PN.	USPAT	2004/08/11 14:36
-	10043	((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:15
-	30291	ldd or (lightly near2 dop\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 14:26
-	3632	(photo near2 resist) near2 (layer or film) same ((photo near2 mask\$1) or mask\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:04
-	16861	((poly near2 crystall\$3) or poly) near2 silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:09
-	458116	tft or (thin near2 film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:15
-	337	(ldd or (lightly near2 dop\$3)) and ((photo near2 resist) near2 (layer or film) same ((photo near2 mask\$1) or mask\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 19:39
-	10	((((ldd or (lightly near2 dop\$3)) and ((photo near2 resist) near2 (layer or film) same ((photo near2 mask\$1) or mask\$1))) and (((poly near2 crystall\$3) or poly) near2 silicon)) and (tft or (thin near2 film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 19:55
-	1	((((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.) and (((((ldd or (lightly near2 dop\$3)) and ((photo near2 resist) near2 (layer or film) same ((photo near2 mask\$1) or mask\$1))) and (((poly near2 crystall\$3) or poly) near2 silicon)) and (tft or (thin near2 film))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 19:40

-	5	((ldd or (lightly near2 dop\$3)) and ((photo near2 resist) near2 (layer or film) same ((photo near2 mask\$1) or mask\$1))) and (((poly near2 crystall\$3) or poly) near2 silicon)) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 19:55
-	38	((ldd or (lightly near2 dop\$3)) and ((photo near2 resist) near2 (layer or film) same ((photo near2 mask\$1) or mask\$1))) and (((poly near2 crystall\$3) or poly) near2 silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:06
-	2	((((photo near2 resist) near2 (layer or film) same ((photo near2 mask\$1) or mask\$1)) same (((poly near2 crystall\$3) or poly) near2 silicon)) and (ldd or (lightly near2 dop\$3))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:07
-	11	((((photo near2 resist) near2 (layer or film) same ((photo near2 mask\$1) or mask\$1)) same (((poly near2 crystall\$3) or poly) near2 silicon)) and (ldd or (lightly near2 dop\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:08
-	64	((photo near2 resist) near2 (layer or film) same ((photo near2 mask\$1) or mask\$1)) same (((poly near2 crystall\$3) or poly) near2 silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:16
-	10301	(source same drain) near10 (ldd or (lightly near2 dop\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:16
-	803	((source same drain) near10 (ldd or (lightly near2 dop\$3))) and (((poly near2 crystall\$3) or poly) near2 silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:17
-	372	((source same drain) near10 (ldd or (lightly near2 dop\$3))) and (((poly near2 crystall\$3) or poly) near2 silicon)) and (tft or (thin near2 film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:17
-	56	((((source same drain) near10 (ldd or (lightly near2 dop\$3))) and (((poly near2 crystall\$3) or poly) near2 silicon)) and (tft or (thin near2 film))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:17
-	3093	(photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 21:07

-	159	((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) and ((source same drain) near10 (ldd or (lightly near2 dop\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:29
-	13	((((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) and ((source same drain) near10 (ldd or (lightly near2 dop\$3)))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:26
-	0	(((((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) and ((source same drain) near10 (ldd or (lightly near2 dop\$3)))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)) not (((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) and ((source same drain) near10 (ldd or (lightly near2 dop\$3))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:29
-	146	((((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) and ((source same drain) near10 (ldd or (lightly near2 dop\$3)))) not (((((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) and ((source same drain) near10 (ldd or (lightly near2 dop\$3)))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:29
-	31623	((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 21:14
-	104	((((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) same ((source same drain) near10 (ldd or (lightly near2 dop\$3))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:42
-	10	(((((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) same ((source same drain) near10 (ldd or (lightly near2 dop\$3)))) and (((poly near2 crystall\$3) or poly) near2 silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:44
-	136	((((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) same (((poly near2 crystall\$3) or poly) near2 silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:44
-	31	(((((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) same (((poly near2 crystall\$3) or poly) near2 silicon)) ) and (ldd or (lightly near2 dop\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:44

-	30	((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) near10 ((source and drain) and (ldd or (lightly near2 dop\$3)))	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:51
-	117	((photo near2 resist) or resist) same ((photo near2 mask\$1) or mask\$1)) near10 ((source and drain) and (ldd or (lightly near2 dop\$3)))	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:55
-	36	((photo near2 resist) or resist) same ((photo near2 mask\$1) or mask\$1)) near10 ((source and drain) and (ldd or (lightly near2 dop\$3))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:52
-	31	(((photo near2 resist) or resist) same ((photo near2 mask\$1) or mask\$1)) near10 ((source and drain) and (ldd or (lightly near2 dop\$3))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)) not ((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) near10 ((source and drain) and (ldd or (lightly near2 dop\$3)))	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:52
-	307	((photo near2 resist) or resist) near10 ((poly near2 crystall\$3) or poly) near2 silicon)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/08/10 20:56
-	198	((photo near2 resist) or resist) near5 ((poly near2 crystall\$3) or poly) near2 silicon)	US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/08/10 20:58
-	9	((photo near2 resist) or resist) near5 ((poly near2 crystall\$3) or poly) near2 silicon) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/08/10 20:56
-	229	(photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near10 ((ion near2 implant\$4) or dop\$)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/08/10 21:22
-	6	(((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near10 ((ion near2 implant\$4) or dop\$)) and (ldd or (lightly near2 dop\$3))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)	US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/08/10 21:09

-	73	((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near10 ((ion near2 implant\$4) or dop\$) ) and (ldd or (lightly near2 dop\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 21:10
-	56	((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near10 ((poly near2 crystall\$3) or poly) near2 silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 21:17
-	7	((photo near2 resist) or resist) near5 (layer or film) same ((photo near2 mask\$1) or mask\$1) near10 ((poly near2 crystall\$3) or poly) near2 silicon) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 21:18
-	94	((photo near2 resist) or resist) near5 (layer or film) same ((photo near2 mask\$1) or mask\$1) near10 ((poly near2 crystall\$3) or poly) near2 silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 21:19
-	157	(photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near5 ((ion near2 implant\$4) or dop\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 21:31
-	10	((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near5 ((ion near2 implant\$4) or dop\$) ) and (((poly near2 crystall\$3) or poly) near2 silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 21:25
-	48	((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near5 ((ion near2 implant\$4) or dop\$) ) and (tft or (thin near2 film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 21:25
-	1	(photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near5 ((ion near2 implant\$4) or dop\$) same ((poly near2 crystall\$3) or poly) near2 silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 21:32
-	20174	((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film) near10 ((photo near2 mask\$1) or mask\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:56
-	16861	((poly near2 crystall\$3) or poly) near2 silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:10
-	303223	(ion near2 implant\$4) or dop\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:16
-	124	(((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) same (((poly near2 crystall\$3) or poly) near2 silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:14
-	84	((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) same (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:18

-	511	((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:14
-	391	(((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:14
-	458116	tft or (thin near2 film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:15
-	191	(((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:47
-	10043	((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:15
-	19	((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:16
-	172	((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))) not (((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:34

	0	((((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))) not (((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.))) not (((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:34
	219	((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) not (((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))) not (((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:35

-	200	((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) not (((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))) not (((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.))) not (((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and (tft or (thin near2 film)))	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:47
-	215	(((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and (tft or (thin near2 film))	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:49
-	16906	((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near5 ((photo near2 mask\$1) or mask\$1)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:57
-	1373	((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near5 ((photo near2 mask\$1) or mask\$1)) same (tft or (thin near2 film))	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:58
-	507	(((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near5 ((photo near2 mask\$1) or mask\$1)) same (tft or (thin near2 film))) and ((ion near2 implant\$4) or dop\$3)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:59
-	5	("5037766"   "5372958"   "5462887"   "5504019"   "5529937").PN.	USPAT	2004/08/11 12:29
-	2	("5985741"   "6066547").PN.	USPAT	2004/08/11 12:39
-	18	("4549843"   "4655874"   "4676868"   "4764483"   "4824802"   "4865952"   "4902899"   "4952274"   "5077234"   "5110410"   "5139608"   "5175122"   "5286581"   "5296092"   "5310621"   "5350486"   "5362591"   "5418093").PN.	USPAT	2004/08/11 12:42
-	5	("5412493"   "5736751"   "5962916"   "6365936"   "6384427").PN.	USPAT	2004/08/11 12:44
-	1	6624443.URPN.	USPAT	2004/08/11 12:45
-	3	("4231811"   "5985766"   "6043000").PN.	USPAT	2004/08/11 12:46
-	0	6410211.URPN.	USPAT	2004/08/11 12:46
-	9	("3920483"   "3997367"   "4035226"   "4137458"   "4140913"   "4144101"   "4149904"   "4163155"   "4182023").PN.	USPAT	2004/08/11 12:47